

Features

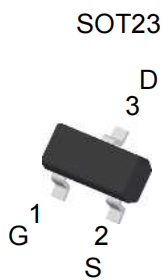
- $V_{DS} = 30V, I_D = 5A$
 $R_{DS(ON)} < 40m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 50m\Omega @ V_{GS}=4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

Typical Applications

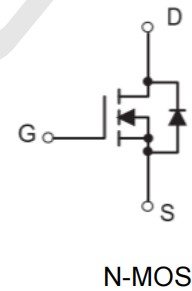
- Load switch
- PWM application

Shipping Quantity

- 3000pcs / Tape & Reel



Circuit Diagram



Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	5	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	15	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	89	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.6	2.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5A$	-	30	40	m Ω
		$V_{GS}=4.5V, I_D=4A$	-	45	50	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	255	-	PF
Output Capacitance	C_{oss}		-	45	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=3\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	4.5	-	nS
Turn-on Rise Time	t_r		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	14.5	-	nS
Turn-Off Fall Time	t_f		-	3.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=5A,$ $V_{GS}=10V$	-	5.2	-	nC
Gate-Source Charge	Q_{gs}		-	0.85	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=5A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	5	A

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)

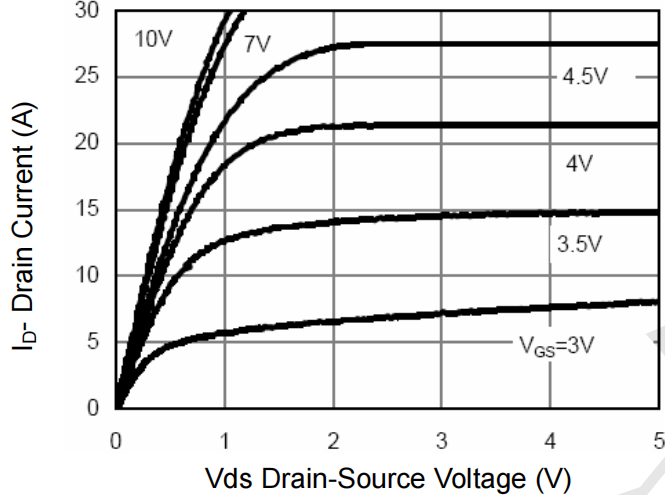


Figure 1 Output Characteristics

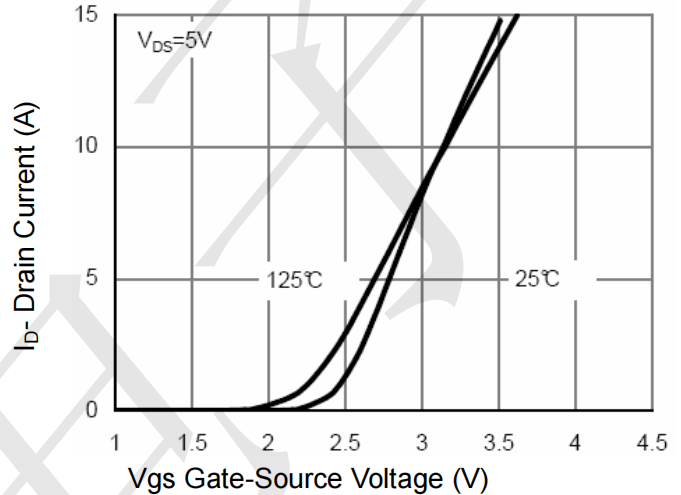


Figure 2 Transfer Characteristics

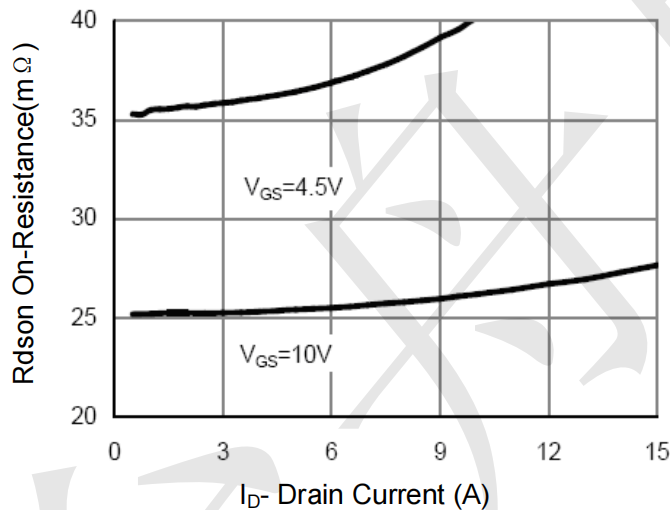


Figure 3 Drain-Source On-Resistance

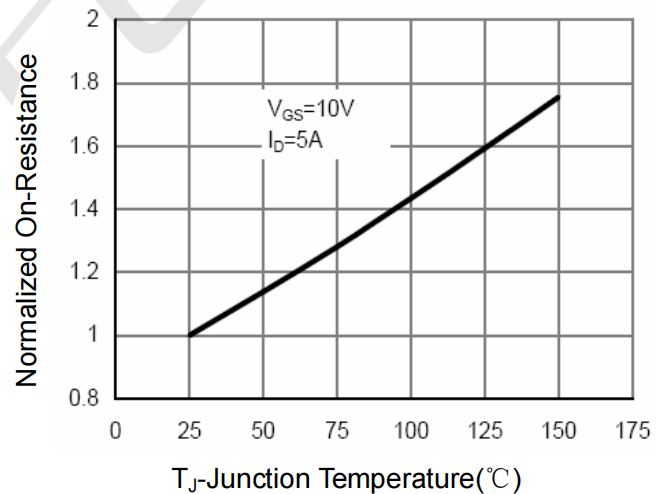


Figure 4 Drain-Source On-Resistance

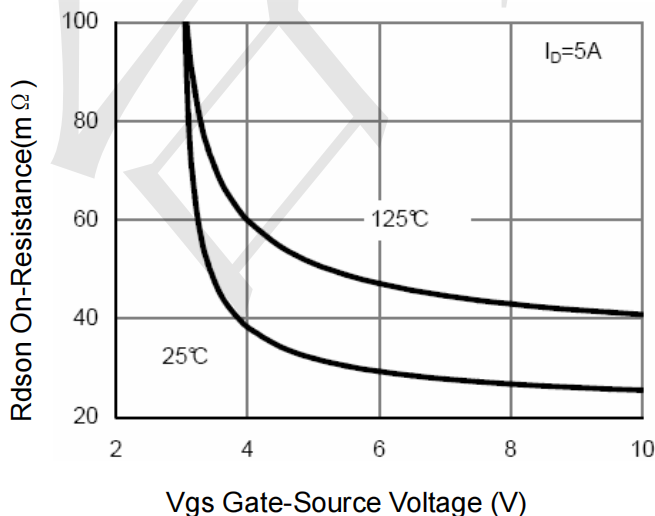


Figure 5 Rdson vs Vgs

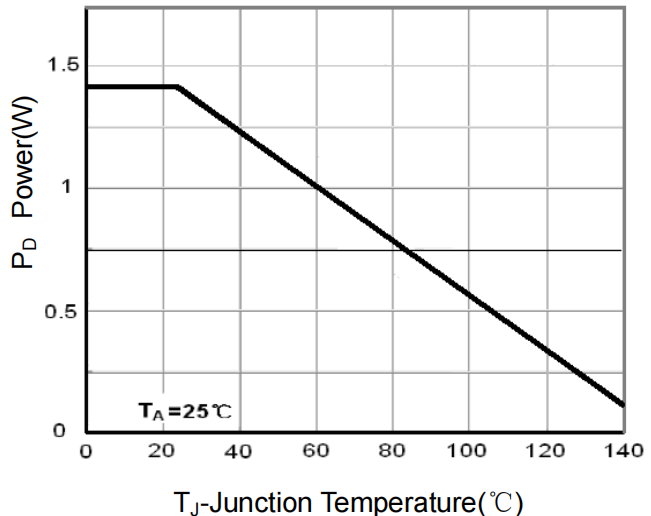
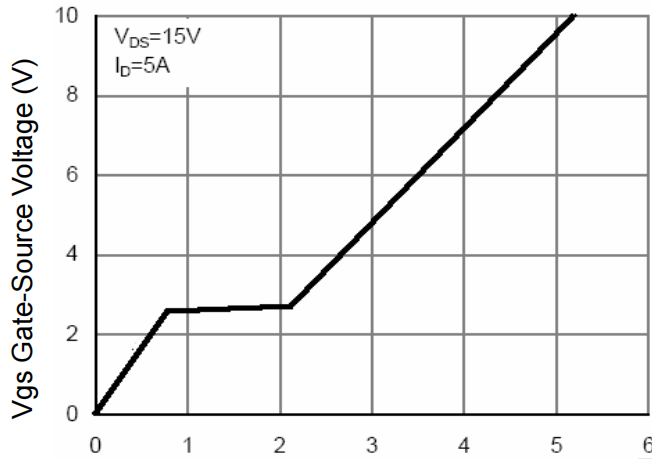
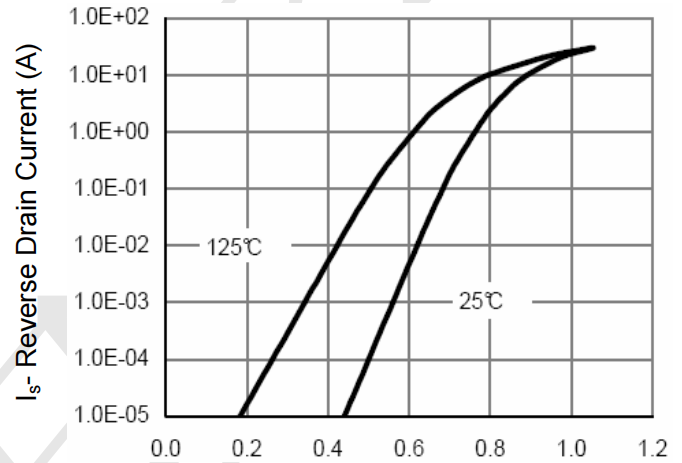


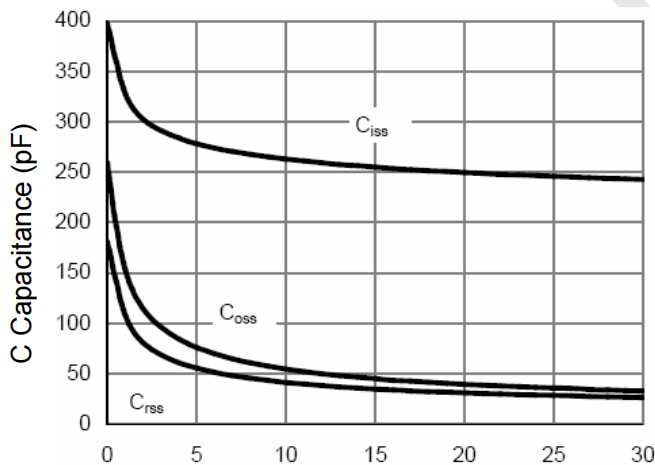
Figure 6 Power Dissipation



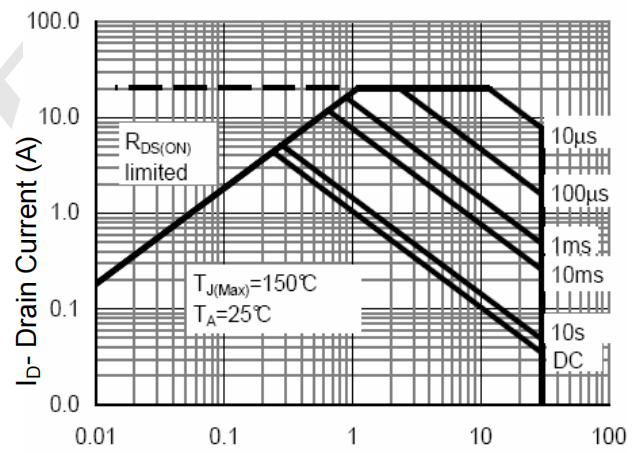
Qg Gate Charge (nC)
Figure 7 Gate Charge



Vds Drain-Source Voltage (V)
Figure 8 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 9 Capacitance vs Vds



Vds Drain-Source Voltage (V)
Figure 10 Safe Operation Area

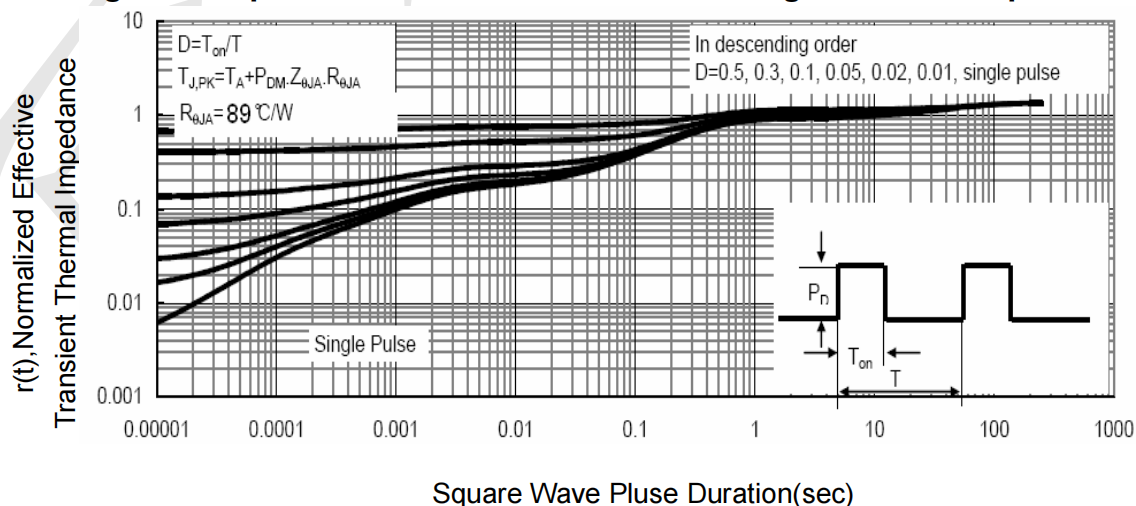
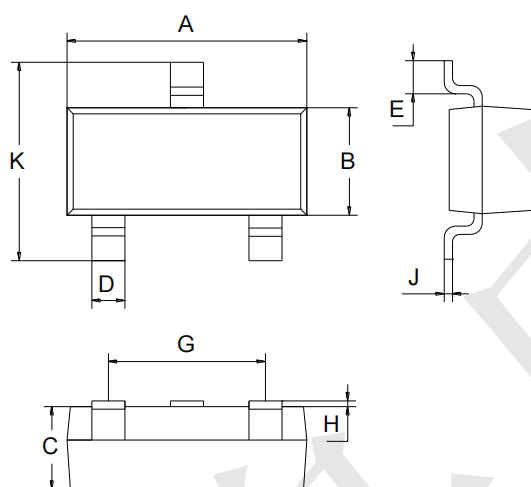


Figure 11 Normalized Maximum Transient Thermal Impedance

Outline Drawing - SOT23



SOT-23		
Dimension	Min.	Max.
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60

Land Pattern - SOT23

